

The i_D versus V_{ds} (V_{sd} for PMOS) curves are determined for the NMOS and PMOS transistor at different values of V_{gs} (V_{sg} for PMOS). The NMOS transistor's behavior is then further examined by acquiring the voltage transfer characteristics of a common-source and common-drain amplifier. Properties of the amplifiers, such as operating regions at different V_{in} values, are observed. A CD4007 MOSFET IC is used for the experiments.